

L Num ber	Hits	Search Text	DB	Time stamp
1	26645	355/\$.c ls.	USPAT; US-PGPUB;	2003/01/10 12:08
2	102	430/13.ccls.	EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB;	2003/01/10 12:09
3	435	257/620.ccls.	EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB;	2003/01/10 12:09
-	1006	235/494.ccls.	EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB;	2002/05/30 17:55
-	0	235/494.ccls. and chiba.in.	EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB;	2002/05/30 17:56
-	0	jp-223380-\$ did.	EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB;	2002/05/30 17:56
-	9	"223380"	EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB;	2002/05/30 17:57
-	0	jp-223380-\$ did.	EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB;	2002/05/30 17:58
-	0	jp-5923512-\$ did.	EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB;	2002/05/30 17:58
-	2	jp-2000223380-\$ did.	EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB;	2002/05/30 18:00

-	0	jp-2175154-\$ did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:00
-	1	jp-3116919-\$ did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:00
-	15423	chiba.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:02
-	818	chiba.in. and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:02
-	58	(chiba.in. and semiconductor) and mark	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:05
-	153	(chiba.in. and semiconductor) and wafer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:06
-	83	235/494.ccls. and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:10
-	8	(235/494.ccls. and semiconductor) and wafer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:06
-	34	(235/494.ccls. and semiconductor) and mark	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 18:47
-	2	6305677.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:16

-	174	269/13.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:18
-	81423	semiconductor adj2 wafer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:19
-	4744	(semiconductor adj2 wafer) and mark	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:19
-	4500	((semiconductor adj2 wafer) and mark) and (semiconductor adj wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:20
-	61	((semiconductor adj2 wafer) and mark) and (semiconductor adj wafer)) and reproduce	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 18:53
-	22	semiconductor adj mark	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 18:52
-	1602	355/53.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:29
-	1154	355/53.ccls. and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:29
-	1052	(355/53.ccls. and semiconductor) and wafer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:29
-	415	((355/53.ccls. and semiconductor) and wafer) and mark	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:30

-	8	((355/53.c ls. and semiconductor) and wafer) and mark) and repr duce	USPAT; US-P PUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:32
-	0	((355/53.ccls. and semiconductor) and wafer) and mark) and efface	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:32
-	5	((355/53.ccls. and semiconductor) and wafer) and mark) and erase	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:34
-	0	((355/53.ccls. and semiconductor) and wafer) and mark) and (reproduce adj erased adj marks)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:35
-	0	((355/53.ccls. and semiconductor) and wafer) and mark) and (reproduce erased marks)) and efface	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:35
-	10	((355/53.ccls. and semiconductor) and wafer) and mark) and (reproduce erased marks)) and notch	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:35
-	300	((355/53.ccls. and semiconductor) and wafer) and mark) and (reproduce erased marks)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:38
-	0	((355/53.ccls. and semiconductor) and wafer) and mark) and (reproduce near erased near marks)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:39
-	0	((355/53.ccls. and semiconductor) and wafer) and mark) and (reproduce same erased same marks)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:39
-	121	((355/53.ccls. and semiconductor) and wafer) and mark) and identical	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:40

	9	((355/53. ccls. and semiconductor) and wafer) and mark) and identical) and reprodu \$2	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:44
	172	((355/53.ccls. and semiconductor) and wafer) and mark) and prevent	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:44
	3	((355/53.ccls. and semiconductor) and wafer) and mark) and prevent) and erase	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:53
	354	355/43.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:53
	84	355/43.ccls. and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:53
	71	(355/43.ccls. and semiconductor) and wafer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:53
	1	((355/43.ccls. and semiconductor) and wafer) and mark) and erase	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:54
	45	((355/43.ccls. and semiconductor) and wafer) and mark	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:58
	25968	355/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:58
	2116	355/\$.ccls. and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:59

	1469	(355/\$.ccls. and semiconductor) and wafer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:59
	497	((355/\$.ccls. and semiconductor) and wafer) and mark	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:59
	8	(((355/\$.ccls. and semiconductor) and wafer) and mark) and erase	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:59
	13	(((355/\$.ccls. and semiconductor) and wafer) and mark) and reproduce	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 19:02
	1	(((355/\$.ccls. and semiconductor) and wafer) and mark) and erase) and (((355/\$.ccls. and semiconductor) and wafer) and mark) and reproduce)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 19:02
	6	(235/494.ccls. and semiconductor) and mark and duplicate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 18:51
	0	(235/494.ccls. and semiconductor) and (duplicate adj mark)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 18:51
	3	(235/494.ccls. and semiconductor) and (duplicate same mark)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 18:51
	0	(semiconductor adj mark) same duplicate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 18:53
	0	(((semiconductor adj2 wafer) and mark) and (semiconductor adj wafer)) and (produce) and (duplicate same mark)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 18:53

	0	((((semiconductor adj2 wafer) and mark) and (semiconductor adj wafer)) and reproduce) and (duplicate near mark)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 18:53
	0	((((semiconductor adj2 wafer) and mark) and (semiconductor adj wafer)) and reproduce) and (duplicate adj mark)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 18:53
	72	((((semiconductor adj2 wafer) and mark) and (semiconductor adj wafer)) and reproduce	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 18:54
	3	((((semiconductor adj2 wafer) and mark) and (semiconductor adj wafer)) and reproduce) and duplicate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 18:54